AUG 3 0 2004		U.S. Paten	PTO/SB/21 (02-04 Approved for use through 07/31/2006. OMB 0651-003 ant and Trademark Office; U.S. DEPARTMENT OF COMMERCE
TRANSMITTAL FORM (to be used for all correspondence after initial in the correspondence after initial ini		Application Number Filing Date First Named Inventor Art Unit Examiner Name	ion of information unless it displays a valid OMB control number 10/689,958 October 20, 2003 Cem Basceri 2812 Unknown
Total Number of Pages in This Submission	FNCI	Attorney Docket Number OSURES (Check all that	Mi22-2417
Fee Transmittal Form Fee Attached Amendment/Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53	L F F F F C C T T T T T T T T T T T T T T	er No. 021567 IS REQUIRED WITH THIS FILI For should a fee be	Other Enclosure(s) (please Identify below): PTO Return Receipt Postcard Form PTO-1449; Copies only of cited articles and applications.
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THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Patent Application Serial No	10/689,958
Filing Date	October 20, 2003
Inventor	Cem Basceri
Assignee	Micron Technology, Inc.
Group Art Unit	2812
Examiner	Unknown
Attorney Docket No	Ml22-2417
Customer No	
Title: Methods of Forming Conductive Met	tal Silicides by Reaction of Metal with
Silicon	

INFORMATION DISCLOSURE STATEMENT References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR §1.56. Pursuant to 1276 OG 55, August 5, 2003, no copies of cited U.S. patents or U.S. patent application publications are included, as the date of filing of this patent application occurs after June 30, 2003. Copies of all other references are attached. No admission is made regarding whether all the listed references are prior art.

Citation of the referenced art is respectfully requested.

This Information Disclosure Statement is being filed before the mailing date of a first Office Action. There, no fee is believed to be required. However, in the event that a fee is required for filing this Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 8/30/64

Mark S. Matkin

Reg. No. 32,268

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APPLICANT: Cem Basceri

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FILING DATE October 20, 2003

GROUP 2812

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ATTY. DOCKET NO. MI22-2417

SERIAL NO. 10/689,958

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PATENT AND TRADEMARK OFFICE MI22-2417

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